

Substitute form 1449/APTO		Complete if Known	
INFORMATION DISCLOSURE STATEMENT BY APPLICANT (use as many sheets as necessary)		Application Number	10/772,882
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		First Named Inventor	Saxder
		Group Art Unit	2811
		Examiner Name	Jerome Jackson, Jr.
Sheet A1 of	Attorney Docket Number	5308-389	

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Examiner Initials*	Cite No.	U.S. Patent Document		Date of Publication of Cited Document MM-DD-YYYY
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	17.	PCT	WO 01/57929 A1		Cree Lighting Company 08-09-2001
	18.	JP	10-050982		Nippon Telegraph & Telephone Corp. 02-20-1998
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Examiner Initials*	Cite No.	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published		
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	21.	Burn et al., "Recessed Gate GaN MODFETS," <i>Solid State Electronics</i> , Vol. 41, No. 2, pp. 247-50 (1997)		
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	24.	Heikman et al., "Polarization Effects in AlGaIn/GaN and GaN/AlGaIn/GaN heterostructures," <i>Journal of Applied Physics</i> , Vol. 93, No. 12, pp. 10114-118 (2003).		
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*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.